



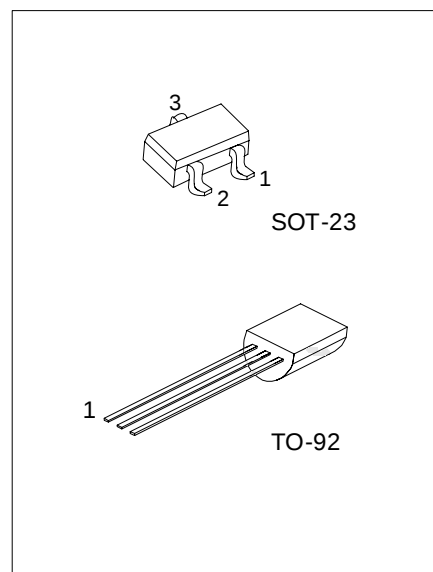
8550S

PNP SILICON TRANSISTOR

LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR

■ FEATURES

- *Collector current up to 700mA
- *Collector-Emitter voltage up to 20 V
- *Complimentary to 8550S



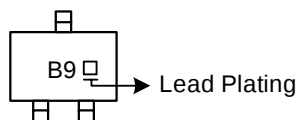
*Pb-free plating product number: 8550SL

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
8550S-x-AE3-R	8550SL-x-AE3-R	SOT-23	E	B	C	Tape Reel
8550S-x-T92-B	8550SL-x-T92-B	TO-92	E	C	B	Tape Box
8550S-x-T92-K	8550SL-x-T92-K	TO-92	E	C	B	Bulk

8550SL-x-AE3-R (1) Packing Type (2) Package Type (3) Rank (4) Lead Plating	(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AE3: SOT-23, T92: TO-92 (3) x: refer to Classification of h_{FE2} (4) L: Lead Free Plating, Blank: Pb/Sn
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■ MARKING (For SOT-23 Package)



■ ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

PARAMETER	SYMBOL	RATING	UNITS
Collector-Base Voltage	V _{CB0}	-30	V
Collector-Emitter Voltage	V _{CE0}	-20	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Dissipation(Ta=25 °C)	SOT-23	350	mW
	TO-92	1	W
Collector Current	I _C	-700	mA
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25 °C, unless otherwise specified)

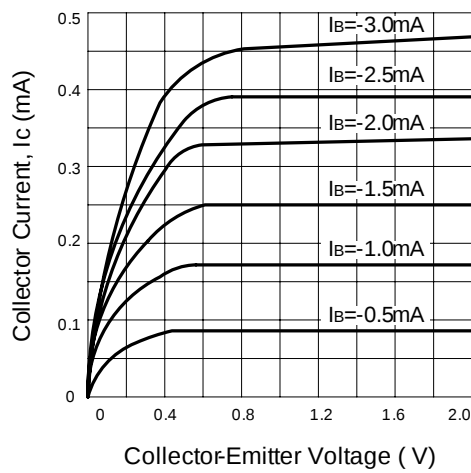
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CB0}	I _C =-100μA, I _E =0	-30			V
Collector-Emitter Breakdown Voltage	BV _{CE0}	I _C =-1mA, I _B =0	-20			V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _E =-100μA, I _C =0	-5			V
Collector Cut-off Current	I _{CB0}	V _{CB} =-30V, I _E =0			-1	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} =-5V, I _C =0			-100	nA
DC Current Gain	h _{FE1}	V _{CE} =-1V, I _C =-1mA	100			
	h _{FE2}	V _{CE} =-1V, I _C =-150 mA	120		400	
	h _{FE3}	V _{CE} =-1V, I _C =-500mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-500mA, I _B =-50mA			-1.2	V
Base-Emitter Saturation Voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA			-1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =-10V, I _C =-50mA	100			MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		9.0		pF

■ CLASSIFICATION OF h_{FE2}

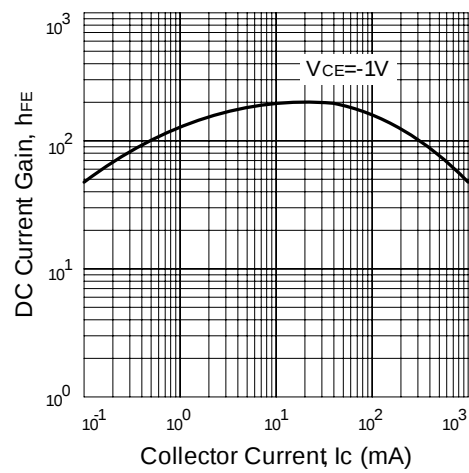
RANK	C	D	E
RANGE	120-200	160-300	280-400

■ TYPICAL CHARACTERISTICS

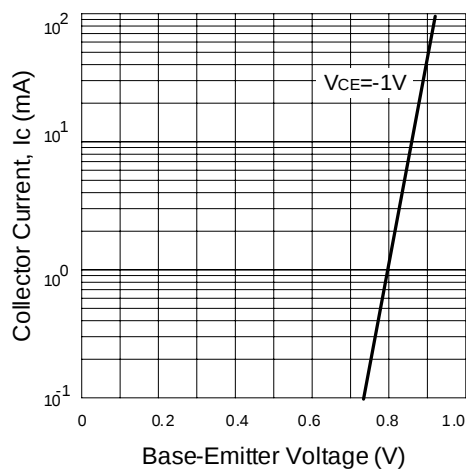
Static Characteristics



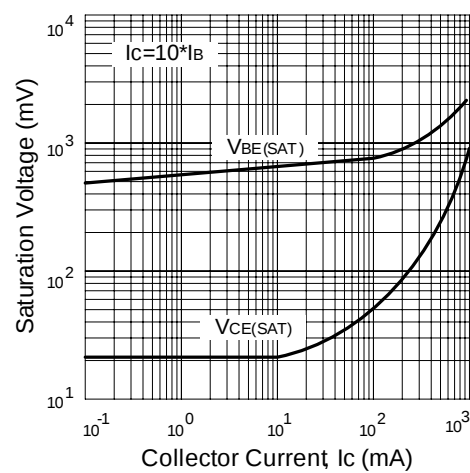
DC Current Gain



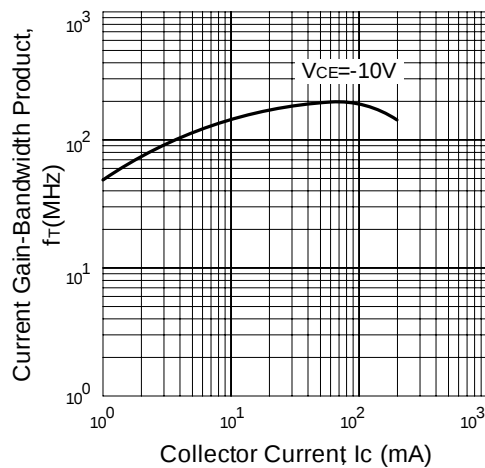
Base-Emitter on Voltage



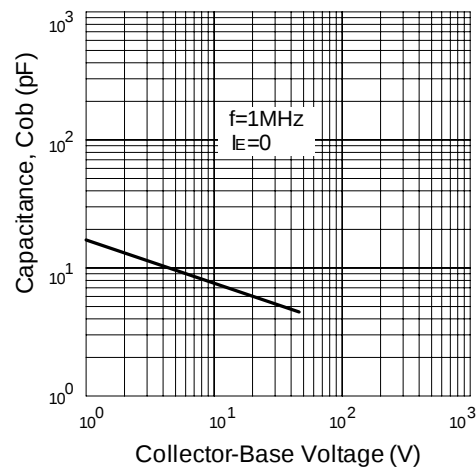
Saturation Voltage



Current Gain-Bandwidth Product



Collector Output Capacitance



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